

AMENDMENTS TO THE SPECIFICATION

Please delete the paragraph bridging pages 26 and 27 and replace it with the following paragraph:

First, as illustrated in ~~FIGURE 18~~ FIGURE 9, and Au/Pt/Ti metalization layer 504 is formed on the bottom surface of a submount 9, which is made of AlN. Then, an Au/Ni plating layer 505 and an Au/Pt/Ti metalization layer 506 are formed on the top surface of the submount 9. The Au/Pt/Ti metalization layer 506 includes areas having greater and smaller thicknesses (having higher and lower surfaces), i.e., the top side of the Au/Pt/Ti metalization layer has a steplike shape. In this specification, the thickness d of the submount 9 does not include the above metalization or plating layers 504 to 506 as illustrated in FIGURE 10.

Please delete the paragraph bridging pages 39 and 40 and replace it with the following paragraph:

The GaN-based semiconductor laser chips LD21 to LD28 each have an identical oscillation wavelength of 400 nm and an identical output power of 50 mW. Divergent laser beams B21 to B28 emitted from the GaN-based semiconductor laser chips LD21 to LD28 are respectively collimated by a microlens array 261. Then, the collimated laser beams B21 to B28 are collected by a condenser lens 262, and converge on an entrance end face of the core 251a of a multimode optical fiber 251. In this example, the optical multiplex system 270 is constituted by the microlens array 261, the condenser lens 262, and the multimode optical fiber 251 comprising the core 251a and cladding 251b. Thus, the laser beams B21 to B28 collected by the condenser

lens 262 as above enter and propagate in the core 251a of the multimode optical fiber 251, in which the laser beams B21 to B28 are optically multiplexed into a single laser beam B20. Then, a laser beam B20 is output from the multimode optical fiber 251.